MAALSS0025



High Dynamic Range Low Noise Amplifier 400 - 500 MHz

Rev. V1

Features

Low Noise Figure: 0.9 dB

High OIP3: +28 dBm at 5 V, 60 mA bias

High Gain: 21 dB

Single Supply: +3 to +8 VDC

Low Cost SOIC-8 Plastic Package

Adjustable current: 20 to 80 mA with external

resistor

Description

M/A-COM's MAALSS0025 is a high dynamic range, low noise GaAs MMIC amplifier in a low cost, surface mount package. It employs external input matching to obtain optimum noise figure performance and operating frequency flexibility.

The MAALSS0025 also features flexible biasing to control the current consumption vs. dynamic range trade-off. The MAALSS0025 can operate from any supply voltage in the 3 V to 8 V range. Its current can be controlled over a range of 20 mA to 80 mA with an external resistor.

The MAALSS0025 is ideally suited for use where low noise figure, high gain, high dynamic range, and low power consumption are required. Typical applications include receiver front ends in CDMA450 base stations. It is also useful as a gain block, buffer, driver, and IF amplifier in both fixed and portable cellular and 450 MHz ISM systems.

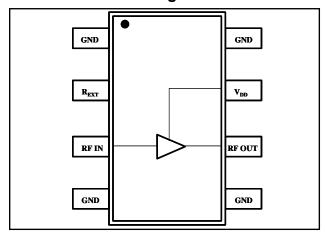
The MAALSS0025 is fabricated using a low-cost 0.5-micron gate length GaAs process. process features full passivation for increased performance reliability.

Ordering Information^{1,2}

Part Number	Package
MAALSS0025	Bulk Packaging
MAALSS0025TR	1000 piece reel
MAALSS0025SMB	Sample Test Board

- 1. Reference Application Note M513 for reel size information.
- 2. All sample boards include 5 loose parts.

Functional Block Diagram



Pin Configuration

Pin No.	Pin Name	Description
1	GND	RF and DC Ground
2	R _{EXT}	External Current Control (optional)
3	RF IN RF Input	
4	GND	RF and DC Ground
5	GND	RF and DC Ground
6	RF OUT	RF Output
7	V_{DD}	Positive supply voltage
8	GND	RF and DC Ground

Absolute Maximum Ratings 3

Parameter	Absolute Maximum	
V_{DD}	+10 VDC	
Input Power	+10 dBm	
Current ⁴	120 mA	
Channel Temperature ⁵	+150°C	
Operating Temperature	-40°C to +85°C	
Storage Temperature	-65°C to +150°C	

- 3. Exceeding any one or combination of these limits may cause permanent damage to this device.
- 4. When pin #2 is used to increase current (see note 6).
- 5. Thermal resistance (θ jc) = +88°C/W.

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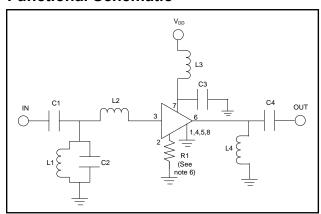
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Electrical Specifications: $T_A = +25^{\circ}C$, $Z_0 = 50 \Omega$, F = 450 MHz, $P_{in} = -30 dBm$

Parameter	Test Conditions	Units	Min	Тур	Max
Gain	5 V, 60 mA ⁶	dB	19	21	24
Noise Figure	5 V, 60 mA ⁶	dB	_	0.9	1.4
Input Return Loss	-	dB	_	9	_
Output Return Loss	_	dB	_	11	_
Output 1 dB Compression	5 V, 60 mA ³	dBm	_	16.5	_
Output IP3	5 V, 60 mA ³	dBm	_	28	_
Input IP3	5 V, 60 mA ³	dBm	3	7	_
Reverse Isolation	-	dB	_	34	_

^{6.} Using external 15-ohm resistor. See functional schematic.

Functional Schematic



Handling Procedures

The following precautions should be observed to avoid damage:

Static Sensitivity

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

External Circuitry Parts List

Part	Value	Purpose	
C1	100 pF	DC Block	
C2	8 pF	Input Matching	
C3	470 pF	Bypass	
C4	4 pF	Output Matching	
L1	22 nH	Input Matching	
L2	43 nH	Input Matching	
L3	12 nH	RF Choke	
L4	11 nH	Output Matching	
R1	15 Ohms	Optional current control ⁷ (see note 6)	

 Pin 2 allows use of an external resistor to ground for optional, higher current. For 20 mA operation, no resistor is

For IDD ~ 40 mA, R2 = 43 ohms;

IDD \sim 60 mA, R2 = 15 ohms;

IDD \sim 80 mA, R2 = 10 ohms.

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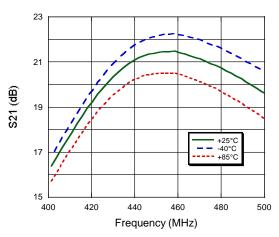
MAALSS0025



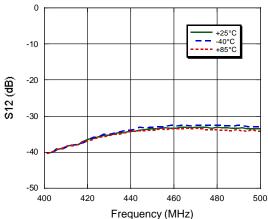
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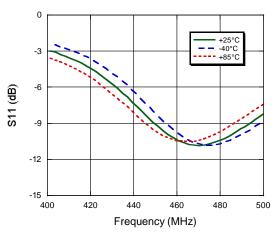
Typical Performance Curves over Temperature



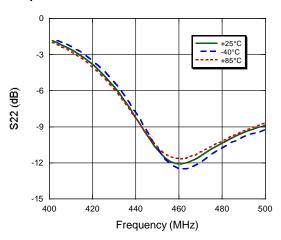
Reverse Isolation



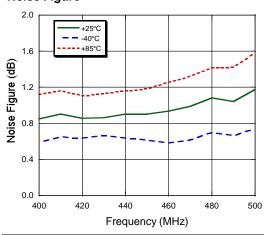
Input Return Loss



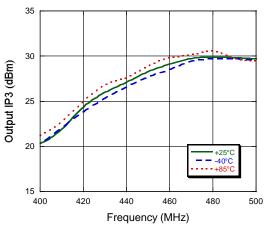
Output Return Loss



Noise Figure



Output IP3



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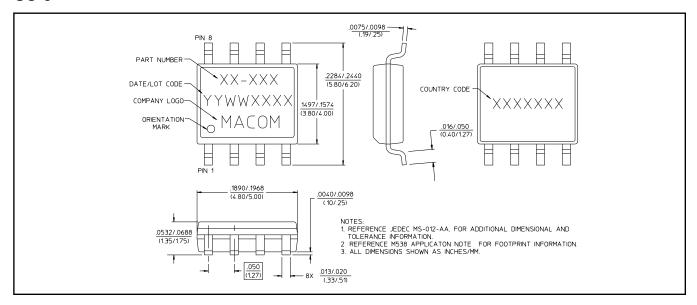
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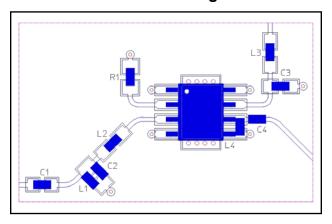
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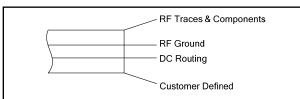
SO-8



Recommended PCB Configuration



Cross Section View



The PCB dielectric between RF traces and RF ground layers should be chosen to reduce RF discontinuities between 50-ohm lines and package pins. M/A-COM recommends an FR-4 dielectric thickness of 0.008" (0.20 mm) yielding a 50-ohm line width of 0.015" (0.38 mm). The recommended RF metalization thickness is 1 ounce copper.

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